

SWITCHING REGULATOR APPLICATIONS

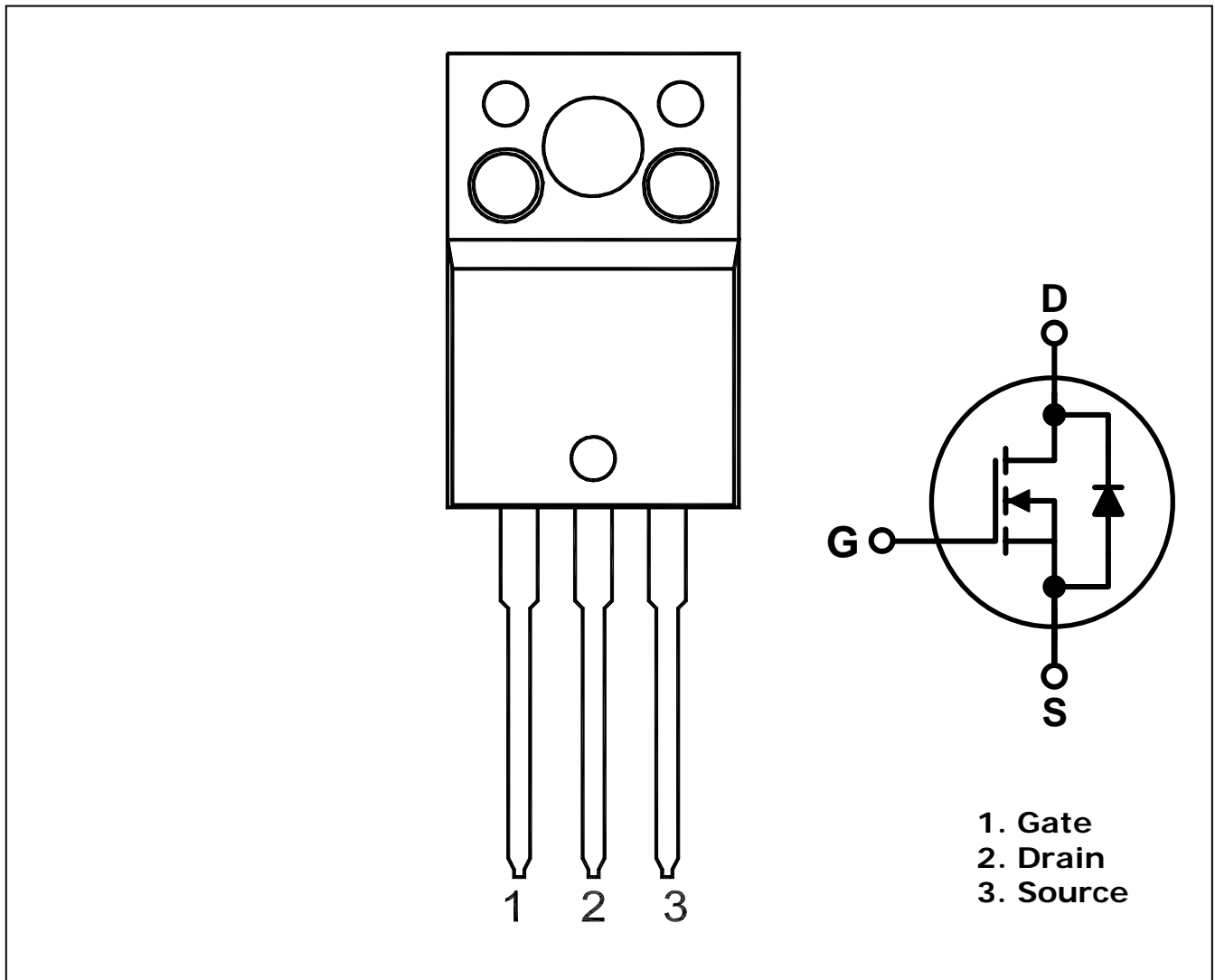
Features

- High Voltage: $BV_{DSS}=650V(\text{Min.})$
- Low C_{rSS} : $C_{rSS}=14.6pF(\text{Typ.})$
- Low gate charge : $Q_g=41nC(\text{Typ.})$
- Low $R_{DS(on)}$: $R_{DS(on)}=0.8\Omega(\text{Max.})$

Ordering Information

| Type NO. | Marking | Package Code |
|----------|---------|--------------|
| SMK1265F | SMK1265 | TO-220F-3L |

PIN Connections



Absolute maximum ratings

(Tc=25°C)

| Characteristic | Symbol | Rating | Unit | |
|----------------------------------|-----------|------------|------|---|
| Drain-source voltage | V_{DSS} | 650 | V | |
| Gate-source voltage | V_{GSS} | ±30 | V | |
| Drain current (DC)* | I_D | (Tc=25°C) | 12 | A |
| | | (Tc=100°C) | 4.5 | A |
| Drain current (Pulsed)* | I_{DM} | 48 | A | |
| Drain power dissipation | P_D | 45 | W | |
| Avalanche current (Single) ② | I_{AS} | 12 | A | |
| Single pulsed avalanche energy ② | E_{AS} | 273 | mJ | |
| Avalanche current (Repetitive) ① | I_{AR} | 12 | A | |
| Repetitive avalanche energy ① | E_{AR} | 7.6 | mJ | |
| Junction temperature | T_J | 150 | °C | |
| Storage temperature range | T_{stg} | -55~150 | | |

* Limited by maximum junction temperature

| Characteristic | | Symbol | Typ. | Max | Unit |
|--------------------|------------------|---------------|------|------|------|
| Thermal resistance | Junction-case | $R_{th(J-C)}$ | - | 2.7 | °C/W |
| | Junction-ambient | $R_{th(J-a)}$ | - | 62.5 | |

Electrical Characteristics

(Tc=25°C)

| Characteristic | Symbol | Test Condition | Min. | Typ. | Max. | Unit | |
|--------------------------------|--------------|--|------|------|-----------|----------|---|
| Drain-source breakdown voltage | BV_{DSS} | $I_D=250\mu A, V_{GS}=0$ | 650 | - | - | V | |
| Gate threshold voltage | $V_{GS(th)}$ | $I_D=250\mu A, V_{DS}=V_{GS}$ | 2.0 | - | 4.0 | V | |
| Drain-source cut-off current | I_{DSS} | $V_{DS}=650V, V_{GS}=0V$ | - | - | 1 | μA | |
| Gate leakage current | I_{GSS} | $V_{DS}=0V, V_{GS}=\pm 30V$ | - | - | ± 100 | nA | |
| Drain-source on-resistance ④ | $R_{DS(ON)}$ | $V_{GS}=10V, I_D=6.0A$ | - | 0.68 | 0.80 | Ω | |
| Forward transfer conductance ④ | g_{fs} | $V_{DS}=10V, I_D=6.0A$ | - | 10 | - | S | |
| Input capacitance | C_{iss} | $V_{GS}=0V, V_{DS}=25V$ $f=1MHz$ | - | 2162 | 2882 | pF | |
| Output capacitance | C_{oss} | | - | 183 | 244 | | |
| Reverse transfer capacitance | C_{rss} | | - | 14.6 | 19.4 | | |
| Turn-on delay time | $t_{d(on)}$ | $V_{DD}=300V, I_D=12A$ $R_G=25\Omega$ | - | 30 | - | ns | |
| Rise time | t_r | | - | 85 | - | | |
| Turn-off delay time | $t_{d(off)}$ | | ③④ | - | 140 | | - |
| Fall time | t_f | | - | 90 | - | | |
| Total gate charge | Q_g | $V_{DS}=480V, V_{GS}=10V$ $I_D=12A$ | - | 41 | 63 | nC | |
| Gate-source charge | Q_{gs} | | - | 13 | - | | |
| Gate-drain charge | Q_{gd} | | ③④ | - | 10.5 | | - |

Source-Drain Diode Ratings and Characteristics

(Tc=25°C)

| Characteristic | Symbol | Test Condition | Min | Typ | Max | Unit |
|---------------------------|----------|--|-----|-----|-----|---------|
| Source current (DC) | I_S | Integral reverse diode in the MOSFET | - | - | 12 | A |
| Source current (Pulsed) ① | I_{SM} | | - | - | 48 | |
| Forward voltage ④ | V_{SD} | $V_{GS}=0V, I_S=12A$ | - | - | 1.4 | V |
| Reverse recovery time | t_{rr} | $I_S=12A, V_{GS}=0,$ $di_S/dt=100A/\mu s$ | - | 510 | - | ns |
| Reverse recovery charge | Q_{rr} | | - | 4.3 | - | μC |

Note ;

- ① Repetitive Rating : Pulse Width Limited by Maximum Junction Temperature
- ② $L=3.5mH, I_{AS}=12A, V_{DD}=50V, R_G=25\Omega$, Starting $T_J = 25^\circ C$
- ③ Pulse Test : Pulse Width < 300us, Duty cycle $\leq 2\%$
- ④ Essentially independent of operating temperature

Electrical Characteristic Curves

Fig. 1 $I_D - V_{DS}$

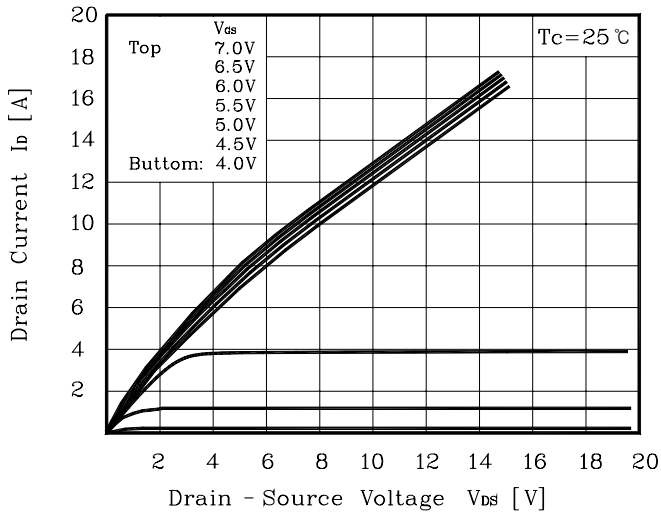


Fig. 2 $I_D - V_{GS}$

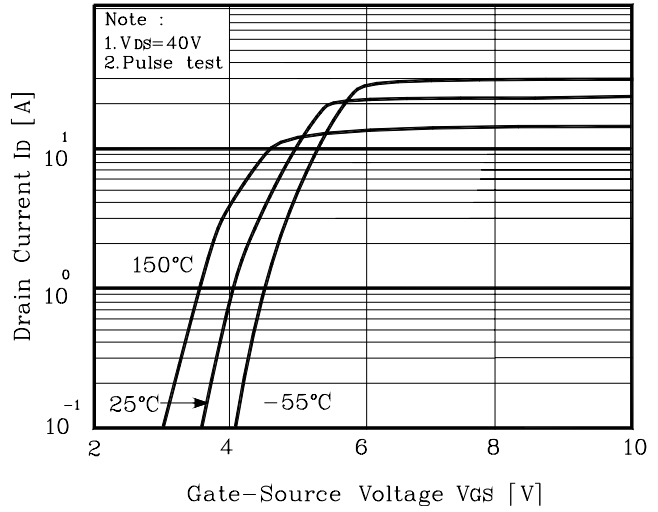


Fig. 3 $R_{DS(on)} - I_D$

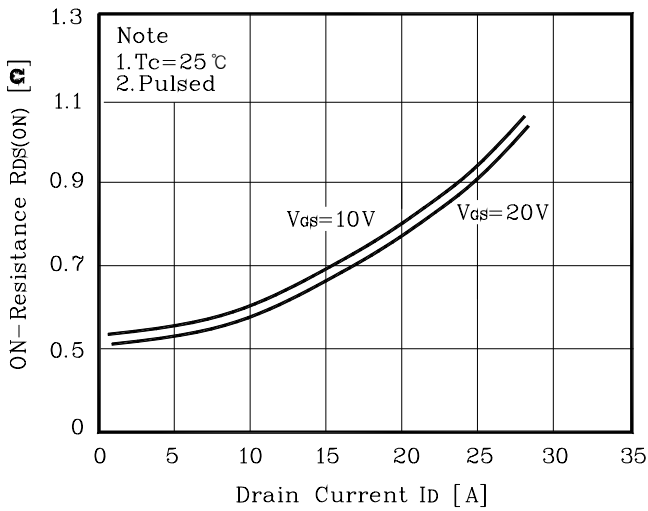


Fig. 4 $I_S - V_{SD}$

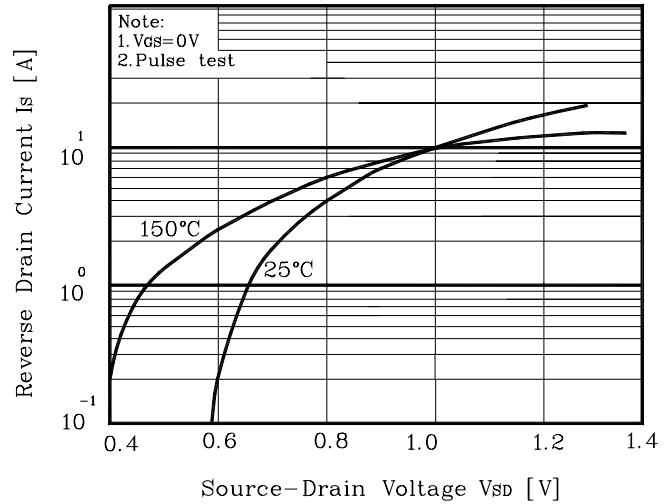


Fig. 5 Capacitance - V_{DS}

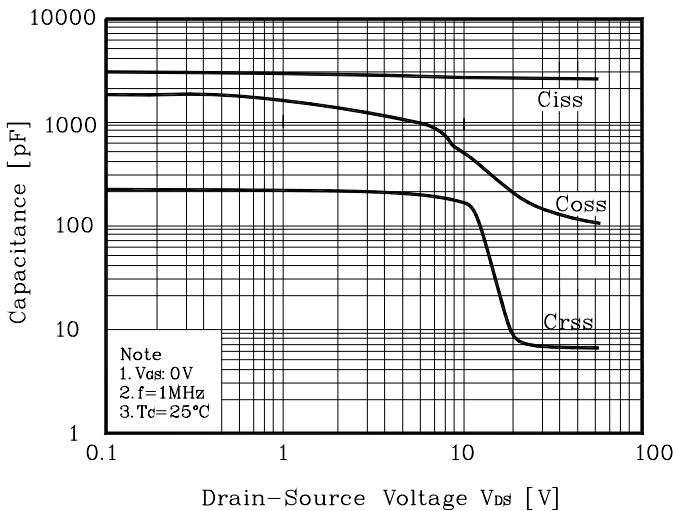
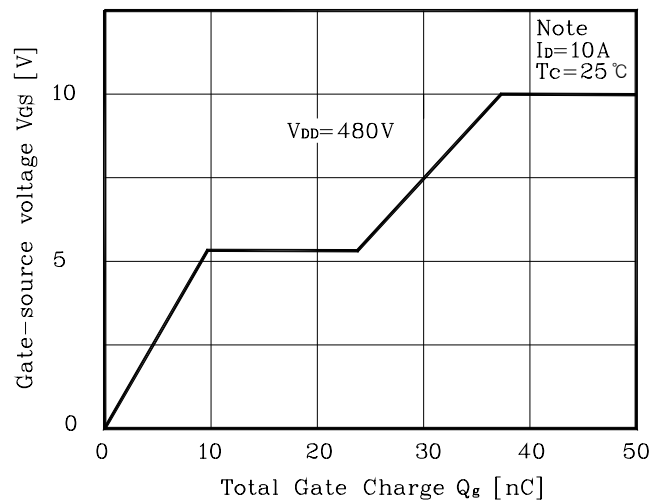


Fig. 6 $V_{GS} - Q_G$



Electrical Characteristic Curves

Fig. 7 $V_{DSS} - T_J$

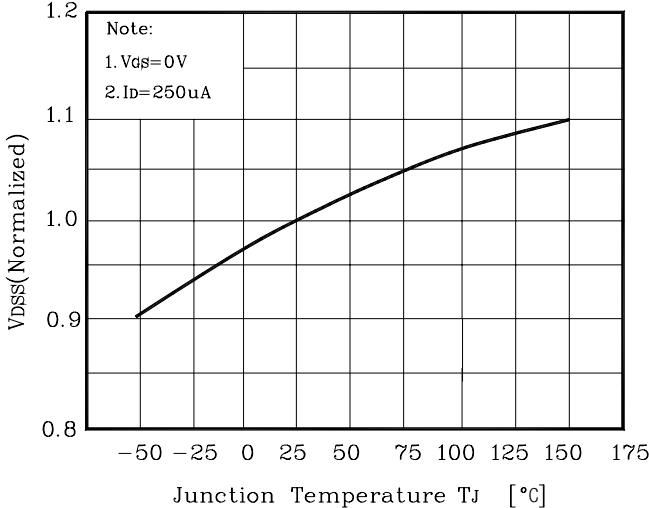


Fig.8 $R_{DS(on)} - T_J$

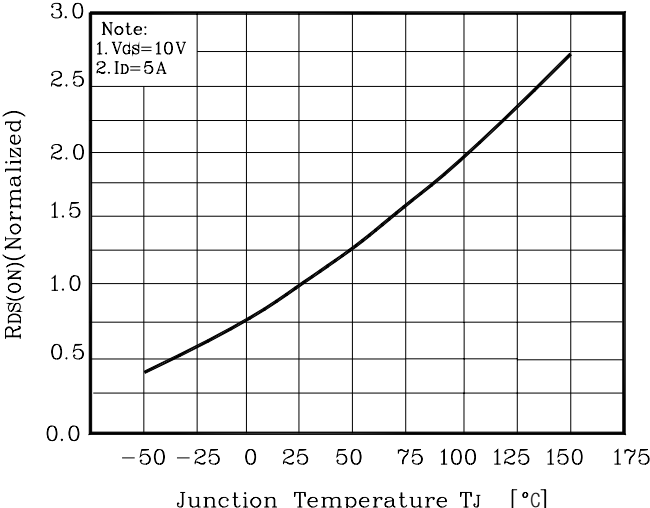


Fig. 9 $I_D - T_C$

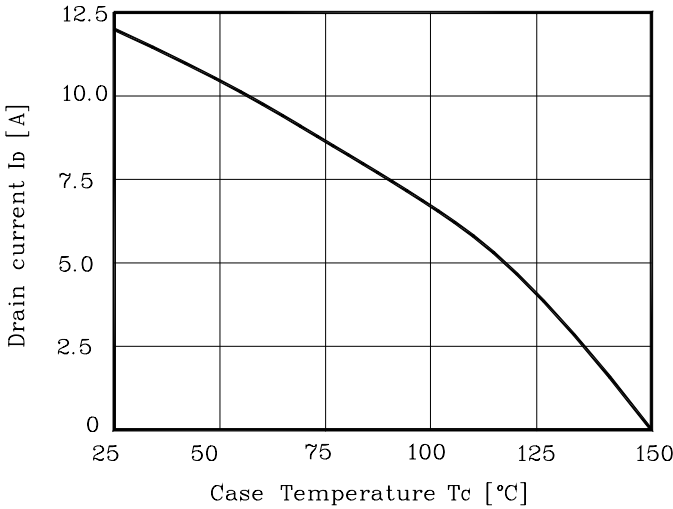


Fig. 10 Safe Operating Area

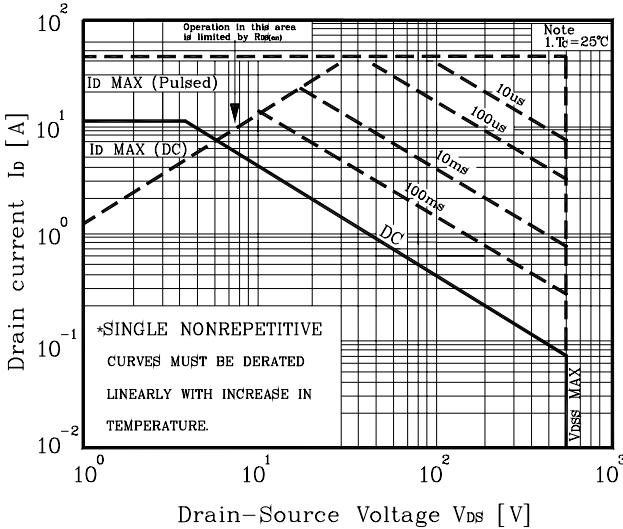


Fig. 11 Gate Charge Test Circuit & Waveform

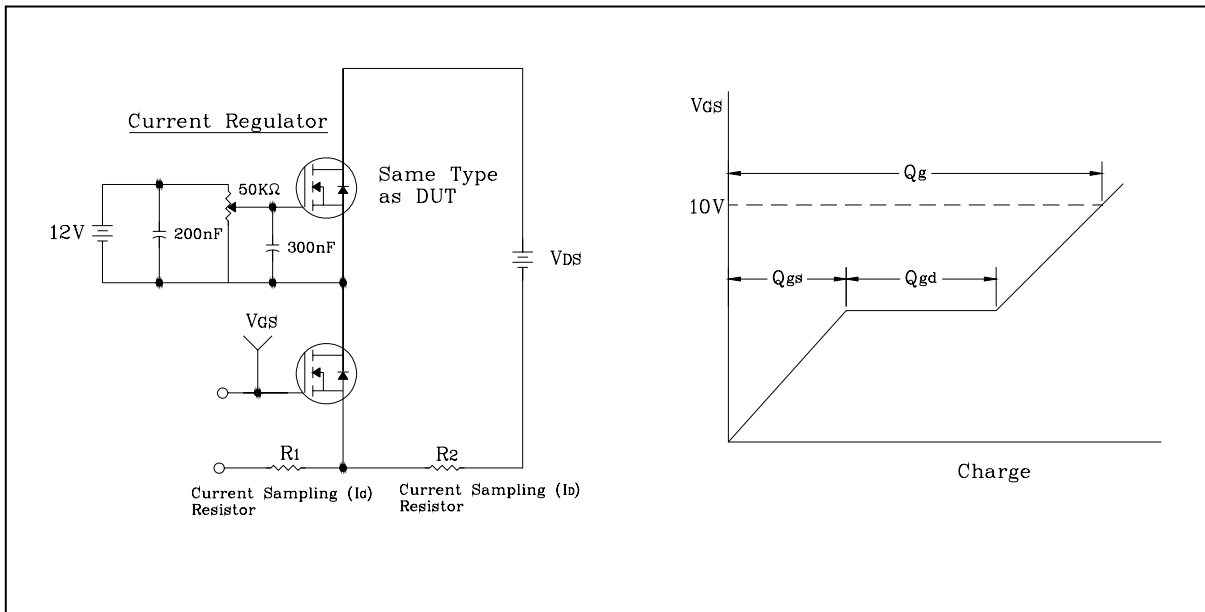


Fig. 12 Resistive Switching Test Circuit & Waveform

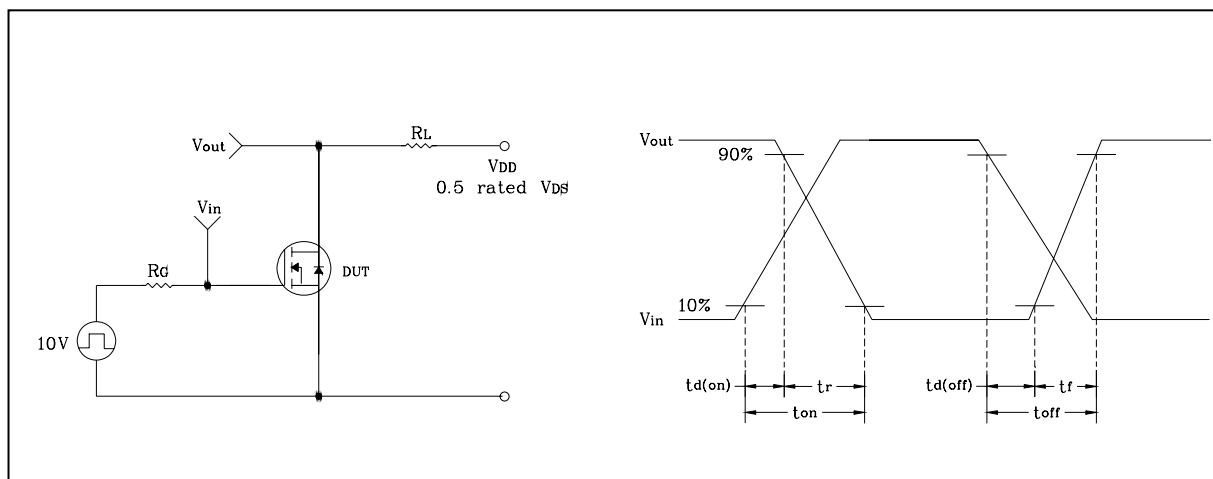


Fig. 13 E_{AS} Test Circuit & Waveform

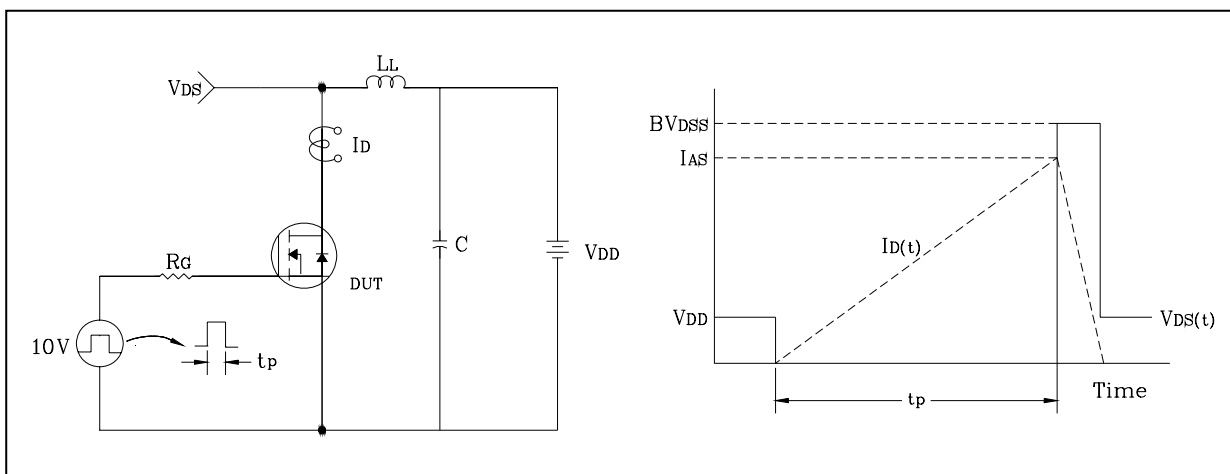
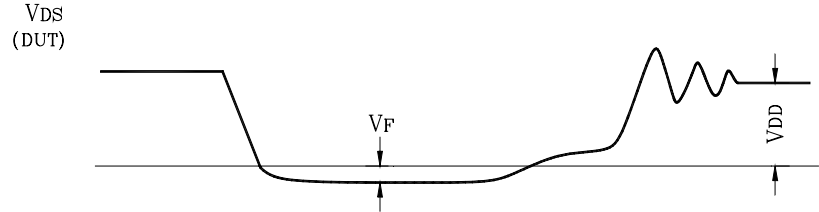
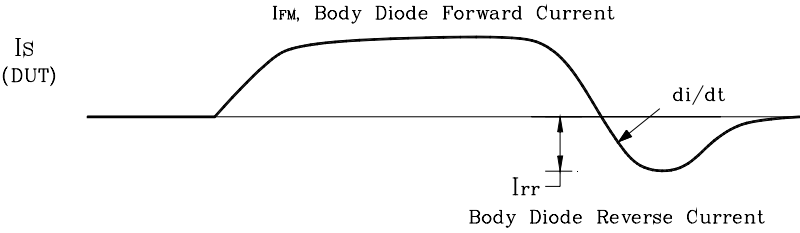
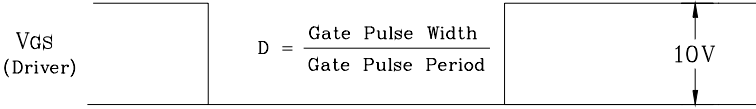
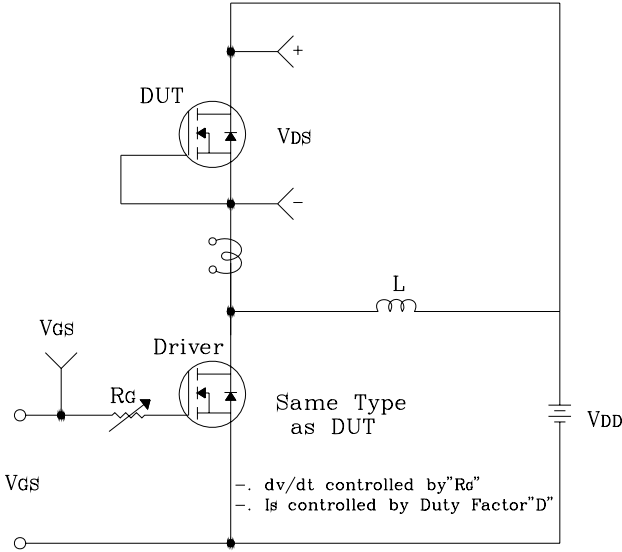
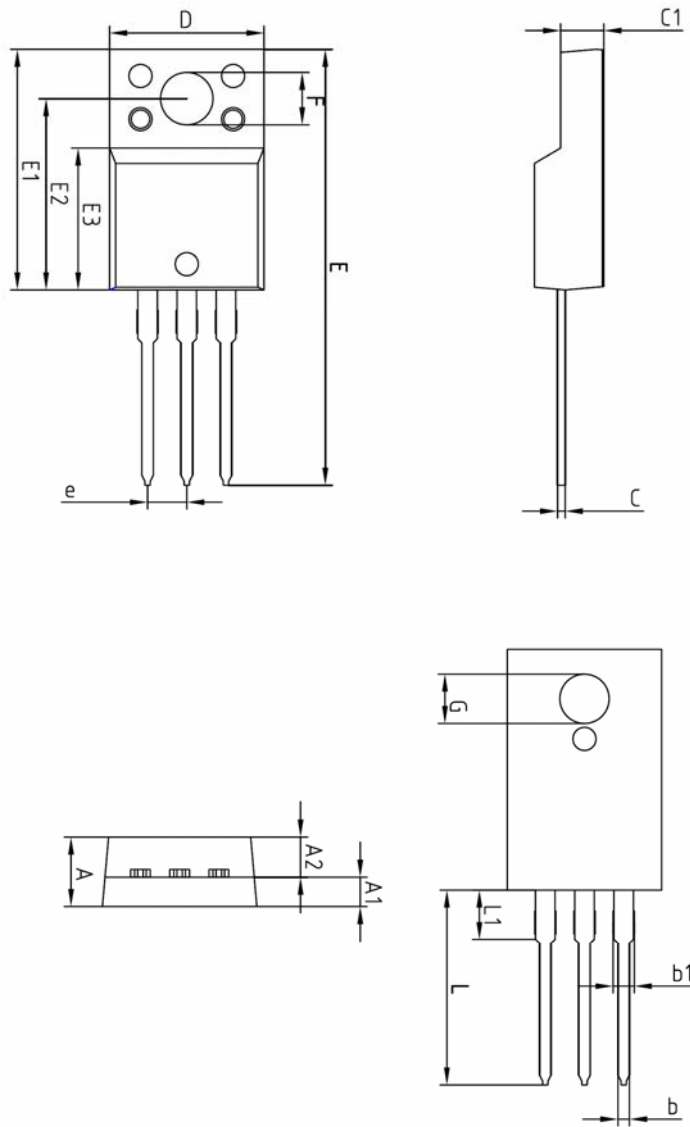


Fig. 14 Diode Reverse Recovery Time Test Circuit & Waveform



Outline Dimension



| SYMBOL | MILLIMETERS | | | NOTE |
|--------|-------------|---------|---------|------|
| | MINIMUM | NOMINAL | MAXIMUM | |
| A | - | - | 4.60 | |
| A1 | 2.45 | 2.50 | 2.55 | |
| A2 | 1.95 | 2.00 | 2.05 | |
| b | 0.65 | 0.75 | 0.85 | |
| b1 | 1.07 | 1.27 | 1.47 | |
| C | 0.40 | 0.50 | 0.60 | |
| C1 | 2.70 | 2.80 | 2.90 | |
| D | 9.90 | 10.00 | 10.10 | |
| E | 28.00 | - | 28.60 | |
| E1 | 15.50 | 15.60 | 15.70 | |
| E2 | 12.30 | 12.40 | 12.50 | |
| E3 | 9.15 | 9.20 | 9.25 | |
| F | 3.30 | 3.40 | 3.50 | |
| G | 3.10 | 3.20 | 3.30 | |
| e | 2.54 BSC | | | |
| L | 12.40 | - | 13.00 | |
| L1 | 3.46 BSC | | | |

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